

PHASE CONTROL THYRISTORS

- **Junction Size** : **Square 340 mils - IR343SG12H/ S1233**
- **Wafer Size** : **4"**
- **V_{RRM}/V_{DRM} Class** : **1200 V**
- **Passivation Process** : **Glassivated MESA**
- **Reference IR Packaged Part** : **50RIA Series**

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{TM} Typical On-state Voltage	1.2V	T _J = 25°C, I _T = 25 A
V _{RRM} /V _{DRM} Direct and Reverse Breakdown Voltage	1200V	T _J = 25°C, I _{DRM} /I _{RRM} = 100 μA (1)
I _{GT} Required DC Gate Current to Trigger	5 to 100 mA	T _J = 25°C, anode supply = 6V, resistive load
V _{GT} Max. Required DC Gate Voltage to Trigger	2V	T _J = 25°C, anode supply = 6V, resistive load
I _H Holding Current Range	5 to 200 mA	Anode supply = 6V, resistive load
I _L Maximum Latching Current	400mA	Anode supply = 6V, resistive load

(1) Nitrogen flow on die edge.

Mechanical Characteristics

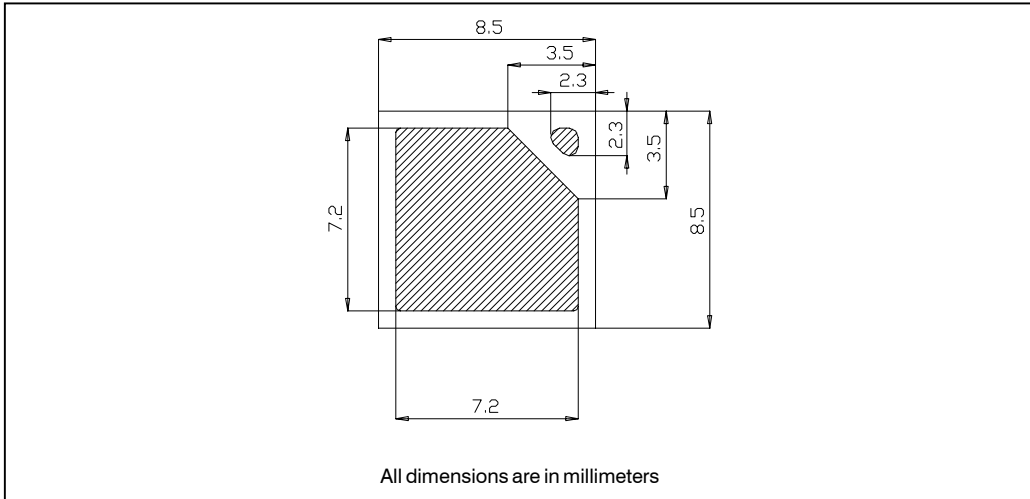
Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 15 KA)
Nominal Front Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 15 KA)
Chip Dimensions	340x340 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	330 μm ± 10 μm
Maximum Width of Sawing Line	130 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

S1233

Bulletin I0142J 01/01

International
IRF Rectifier

Outline Table



Wafer Layout

